

4V Drive Nch MOSFET

RSD100N10

Structure

Silicon N-channel MOSFET

Features

- 1) Low on-resistance.
- 2) 4V drive.
- 3) High power package.

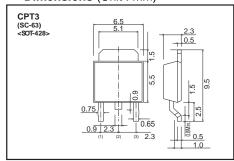
Application

Switching

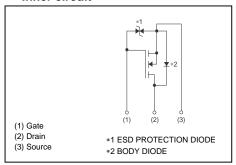
Packaging specifications

| | Package | Taping | |
|----------|------------------------------|--------|--|
| Type | Code | TL | |
| | Basic ordering unit (pieces) | 2500 | |
| RSD100N1 | 0 | | |

• Dimensions (Unit : mm)



• Inner circuit



● Absolute maximum ratings (Ta = 25°C)

| Parameter | | Symbol | Limits | Unit |
|------------------------------|------------|--------------------|------------------|------|
| Drain-source voltage | | V_{DSS} | 100 | V |
| Gate-source voltage | | V_{GSS} | ±20 | V |
| Drain current | Continuous | I _D *3 | ±10 | Α |
| | Pulsed | I _{DP} *1 | ±20 | Α |
| Source current | Continuous | I _S *3 | 10 | Α |
| (Body Diode) | Pulsed | I _{SP} *1 | 20 | Α |
| Power dissipation | | P _D *2 | 20 | W |
| Channel temperature | | Tch | 150 | °C |
| Range of storage temperature | | Tstg | Tstg -55 to +150 | |

^{*1} $P_W \le 10 \mu s$, Duty cycle $\le 1\%$

• Thermal resistance

| Parameter | Symbol | Limits | Unit |
|-----------------|-------------|--------|------|
| Channel to Case | Rth (ch-c)* | 6.25 | °C/W |

^{*} T_C=25°C

^{*2} T_C=25°C

^{*3} Please use within the range of SOA.

● Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|-----------------------|------|------|------|------|--|
| Gate-source leakage | I _{GSS} | - | - | ±10 | μA | $V_{GS}=\pm20V$, $V_{DS}=0V$ |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 100 | - | - | ٧ | I _D =1mA, V _{GS} =0V |
| Zero gate voltage drain current | I _{DSS} | 1 | - | 1 | μA | V_{DS} =100V, V_{GS} =0V |
| Gate threshold voltage | V _{GS (th)} | 1 | - | 2.5 | ٧ | V_{DS} =10V, I_{D} =1mA |
| Static drain-source on-state resistance | 4 | 1 | 95 | 133 | | I _D =5A, V _{GS} =10V |
| | R _{DS (on)} | 1 | 100 | 140 | mΩ | I _D =5A, V _{GS} =4.5V |
| | | 1 | 105 | 147 | | $I_D=5A, V_{GS}=4V$ |
| Forward transfer admittance | IY _{fs} I* | 4.5 | - | - | S | V_{DS} =10V, I_{D} =5A |
| Input capacitance | C _{iss} | 1 | 700 | - | pF | V _{DS} =25V |
| Output capacitance | C _{oss} | 1 | 65 | - | pF | V _{GS} =0V |
| Reverse transfer capacitance | C _{rss} | 1 | 40 | - | pF | f=1MHz |
| Turn-on delay time | t _{d(on)} * | • | 10 | - | ns | V _{DD} ≒ 50V, I _D =5A |
| Rise time | t _r * | 1 | 17 | - | ns | V _{GS} =10V |
| Turn-off delay time | t _{d(off)} * | 1 | 50 | - | ns | $R_L=10\Omega$ |
| Fall time | t _f * | 1 | 20 | - | ns | $R_G=10\Omega$ |
| Total gate charge | Q _g * | - | 18 | - | nC | V _{DD} ≒ 50V, I _D =10A |
| Gate-source charge | Q _{gs} * | - | 2 | _ | nC | V _{GS} =10V |
| Gate-drain charge | Q _{gd} * | - | 4.5 | _ | nC | |

^{*}Pulsed

●Body diode characteristics (Source-Drain)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|-------------------|------|------|------|------|--|
| Forward Voltage | V _{SD} * | - | - | 1.5 | V | I _s =10A, V _{GS} =0V |

^{*}Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

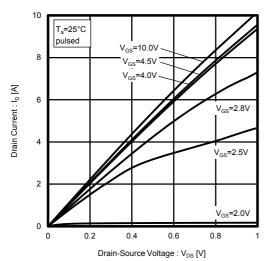


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

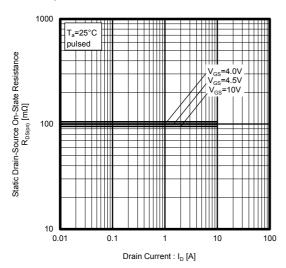


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

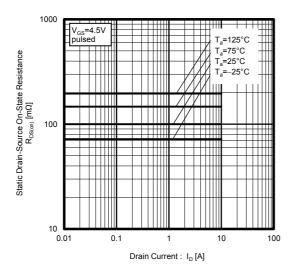


Fig.2 Typical Output Characteristics (${\rm I\hspace{-.1em}I}$)

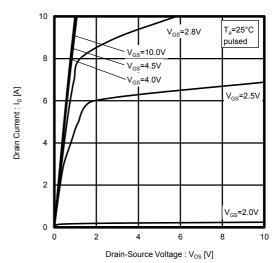


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

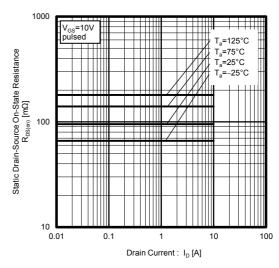


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

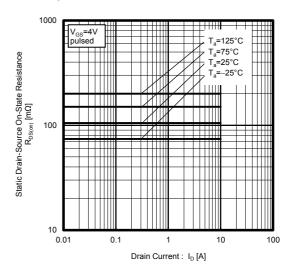


Fig.7 Forward Transfer Admittance vs. Drain Current

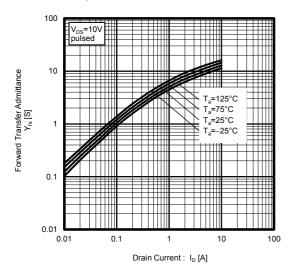


Fig.9 Source Current vs. Source-Drain Voltage

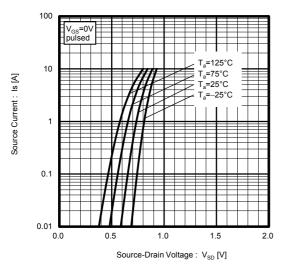


Fig.11 Switching Characteristics

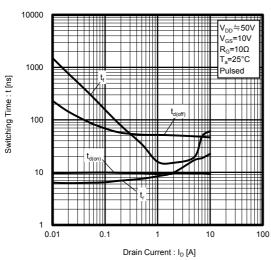


Fig.8 Typical Transfer Characteristics

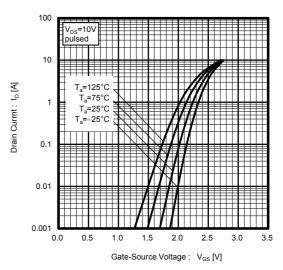


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

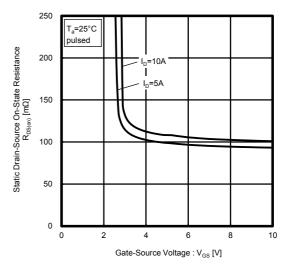


Fig.12 Dynamic Input Characteristics

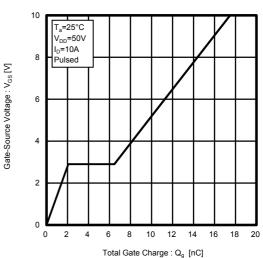


Fig.13 Typical Capacitance vs. Drain-Source Voltage

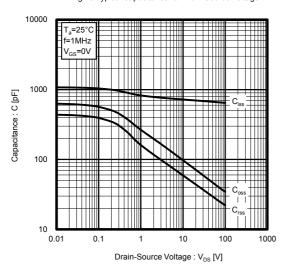


Fig.15 Maximum Safe Operating Area

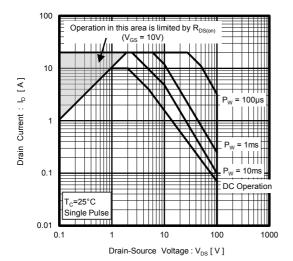
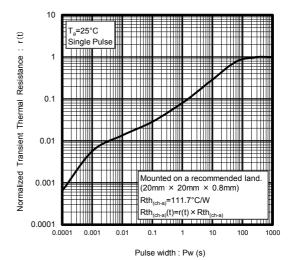


Fig.14 Normalized Transient Thermal Resistance v.s. Pulse Width



Measurement circuits

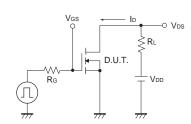


Fig.1-1 Switching Time Measurement Circuit

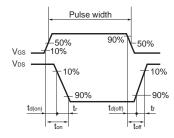


Fig.1-2 Switching Waveforms

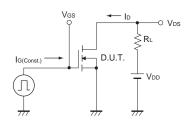


Fig.2-1 Gate Charge Measurement Circuit

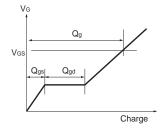


Fig.2-2 Gate Charge Waveform

6/6

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